

**25.** The method of claim **20** wherein the first conductivity type is n type and the epitaxial material is p type.

**26.** The method of claim **20** wherein a dopant concentration in at least one of the first III-nitride epitaxial layer or the one or more additional III-nitride epitaxial layers is non-uniform.

**27.** The method of claim **20** wherein the thickness of the first III-nitride epitaxial layer is between 1  $\mu\text{m}$  and 100  $\mu\text{m}$ .

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